OM SENI

# AOD444

## 60V N-Channel MOSFET

### General Description

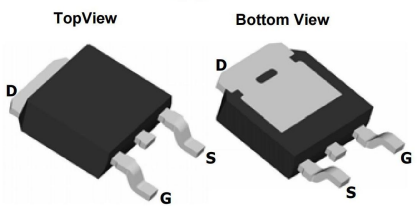
The AOD444combine advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. Those devices are suitable for use in PWM, load switching and general purpose applications.

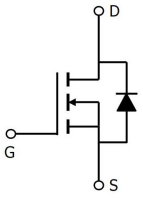
### Product Summary

| | |
|---|---|
| $V_{DS}$ | 60V |
| $I_D$ (at $V_{GS}$=10V) | 12A |
| $R_{DS(ON)}$ (at $V_{GS}$=10V) | < 60mΩ |
| $R_{DS(ON)}$ (at $V_{GS}$ = 4.5V) | < 85mΩ |

100% UIS Tested
100% Rg Tested

TO252
DPAK




| Orderable Part Number | Package Type | Form | Minimum Order Quantity |
|---|---|---|---|
| | TO-252 | Tape & Reel | 2500 |

**Absolute Maximum Ratings $T_A$=25°C unless otherwise noted**

| Parameter | | Symbol | Maximum | Units |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DS}$ | 60 | V |
| Gate-Source Voltage | | $V_{GS}$ | ±20 | V |
| Continuous Drain Current [G] | $T_C$=25°C | $I_D$ | 12 | A |
| | $T_C$=100°C | | 9 | |
| Pulsed Drain Current [C] | | $I_{DM}$ | 30 | |
| Continuous Drain Current | $T_A$=25°C | $I_{DSM}$ | 4 | A |
| | $T_A$=70°C | | 3 | |
| Avalanche Current [C] | | $I_{AS}$, $I_{AR}$ | 19 | A |
| Avalanche energy L=0.1mH [C] | | $E_{AS}$, $E_{AR}$ | 18 | mJ |
| Power Dissipation [B] | $T_C$=25°C | $P_D$ | 20 | W |
| | $T_C$=100°C | | 10 | |
| Power Dissipation [A] | $T_A$=25°C | $P_{DSM}$ | 2.1 | W |
| | $T_A$=70°C | | 1.3 | |
| Junction and Storage Temperature Range | | $T_J$, $T_{STG}$ | -55 to 175 | °C |

**Thermal Characteristics**

| Parameter | | Symbol | Typ | Max | Units |
|---|---|---|---|---|---|
| Maximum Junction-to-Ambient [A] | t ≤ 10s | $R_{\theta JA}$ | 17.4 | 30 | °C/W |
| Maximum Junction-to-Ambient [A D] | Steady-State | | 50 | 60 | °C/W |
| Maximum Junction-to-Case | Steady-State | $R_{\theta JC}$ | 4 | 7.5 | °C/W |

OM SENI

**Electrical Characteristics ($T_J$=25°C unless otherwise noted)**

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **STATIC PARAMETERS** | | | | | | |
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | $I_D$=250μA, $V_{GS}$=0V | 60 | | | V |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$=48V, $V_{GS}$=0V | | | 1 | μA |
| | | $T_J$=55°C | | | 5 | |
| $I_{GSS}$ | Gate-Body leakage current | $V_{DS}$=0V, $V_{GS}$= ±20V | | | 100 | nA |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$=$V_{GS}$ $I_D$=250μA | 1 | 2.4 | 3 | V |
| $I_{D(ON)}$ | On state drain current | $V_{GS}$=10V, $V_{DS}$=5V | 30 | | | A |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | $V_{GS}$=10V, $I_D$=12A | | 47 | 60 | mΩ |
| | | $T_J$=125°C | | 85 | 100 | |
| | | $V_{GS}$=4.5V, $I_D$=6A | | 67 | 85 | mΩ |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$=5V, $I_D$=20A | | 14 | | S |
| $V_{SD}$ | Diode Forward Voltage | $I_S$=1A,$V_{GS}$=0V | | 0.74 | 1 | V |
| $I_S$ | Maximum Body-Diode Continuous Current | | | | 12 | A |
| **DYNAMIC PARAMETERS** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{GS}$=0V, $V_{DS}$=30V, f=1MHz | 360 | 450 | 540 | pF |
| $C_{oss}$ | Output Capacitance | | 40 | 61 | 80 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | 16 | 27 | 40 | pF |
| $R_g$ | Gate resistance | $V_{GS}$=0V, $V_{DS}$=0V, f=1MHz | 0.6 | 1.4 | 2.0 | Ω |
| **SWITCHING PARAMETERS** | | | | | | |
| $Q_g$(10V) | Total Gate Charge | $V_{GS}$=10V, $V_{DS}$=30V, $I_D$=12A | | 7.5 | 10 | nC |
| $Q_g$(4.5V) | Total Gate Charge | | | 3.8 | 5 | nC |
| $Q_{gs}$ | Gate Source Charge | | | 1.2 | | nC |
| $Q_{gd}$ | Gate Drain Charge | | | 1.9 | | nC |
| $t_{D(on)}$ | Turn-On DelayTime | $V_{GS}$=10V, $V_{DS}$=30V, $R_L$=2.5Ω, $R_{GEN}$=3Ω | | 4.2 | | ns |
| $t_r$ | Turn-On Rise Time | | | 3.4 | | ns |
| $t_{D(off)}$ | Turn-Off DelayTime | | | 16 | | ns |
| $t_f$ | Turn-Off Fall Time | | | 2 | | ns |
| $t_{rr}$ | Body Diode Reverse Recovery Time | $I_F$=12A, dI/dt=100A/μs | | 27 | 35 | ns |
| $Q_{rr}$ | Body Diode Reverse Recovery Charge | $I_F$=12A, dI/dt=100A/μs | | 30 | | nC |

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in $^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A$ =25°C. The Power dissipation $P_{DSM}$ is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B. The power dissipation $P_D$ is based on $T_{J(MAX)}$=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=175°C. Ratings are based on low frequency and duty cycles to keep initial $T_J$ =25°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=175°C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in $^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A$=25°C.

OM SENI

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

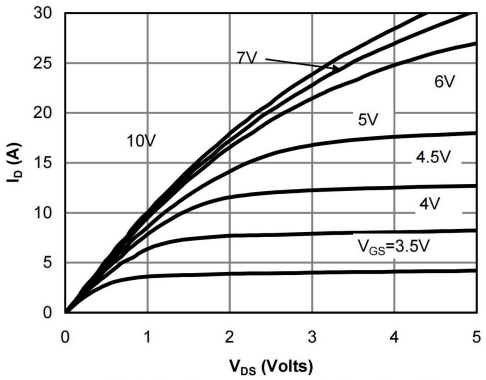



Fig 1: On-Region Characteristics (Note E)

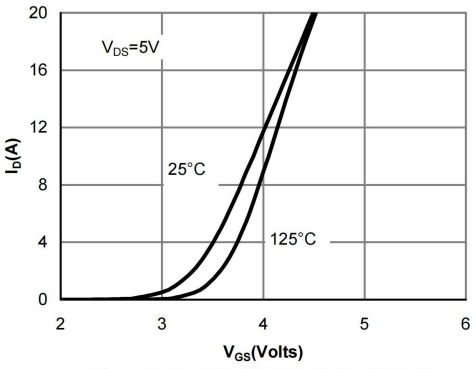



Figure 2: Transfer Characteristics (Note E)

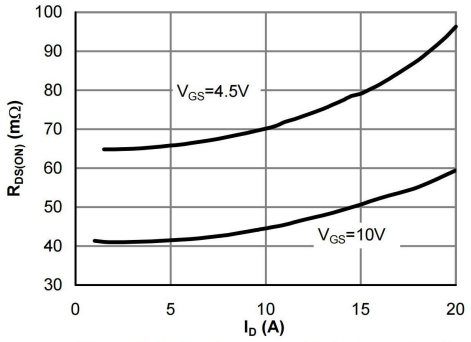



Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

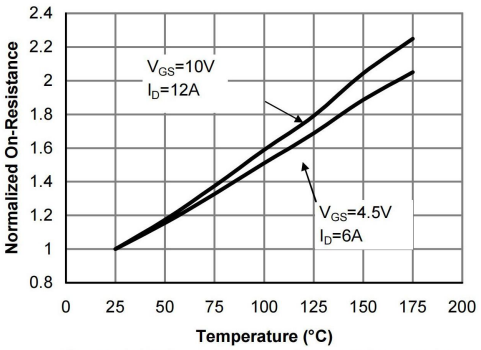



Figure 4: On-Resistance vs. Junction Temperature (Note E)

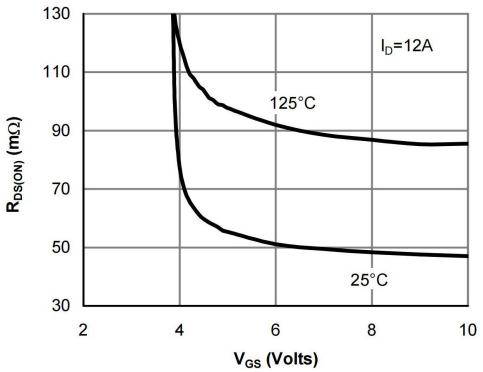



Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

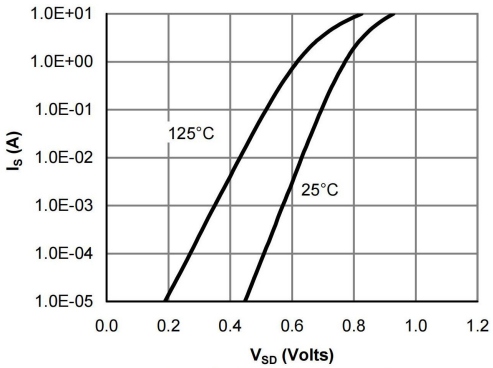



Figure 6: Body-Diode Characteristics (Note E)

OM SENI

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

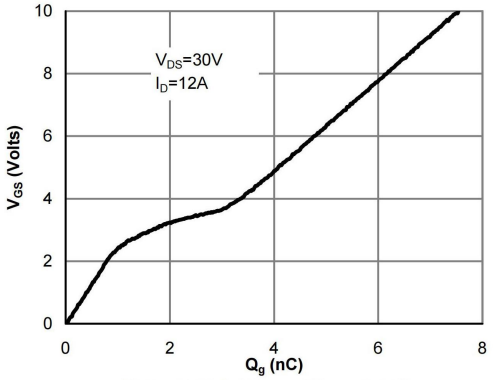



Figure 7: Gate-Charge Characteristics

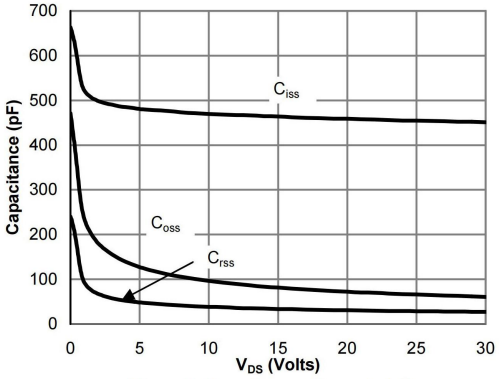



Figure 8: Capacitance Characteristics

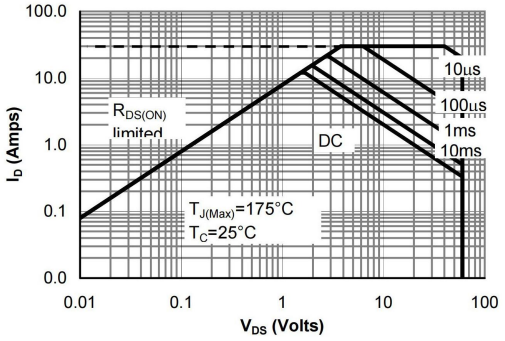



Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

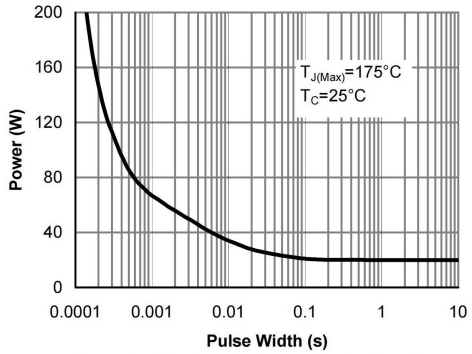



Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

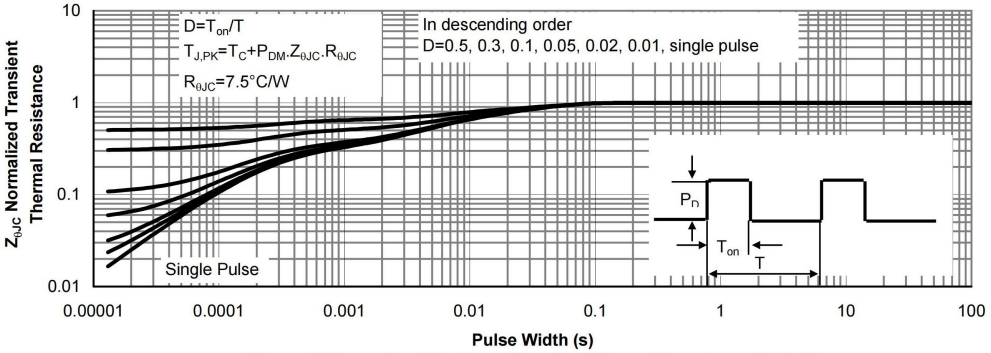



Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

OM SENI

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

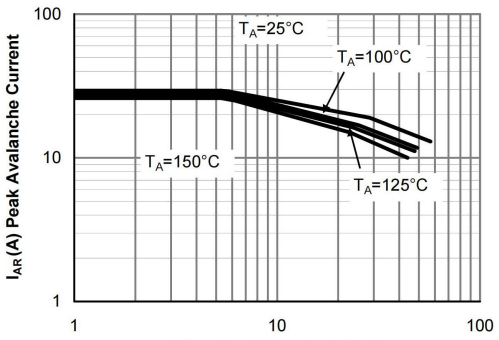



Figure 12: Single Pulse Avalanche capability (Note C)

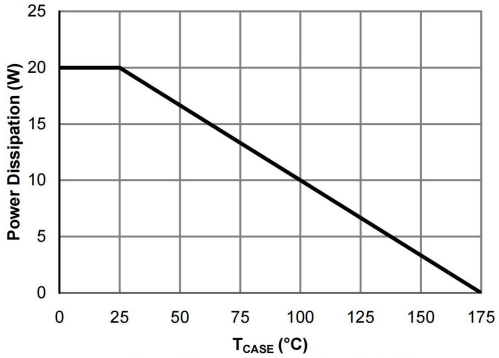



Figure 13: Power De-rating (Note F)

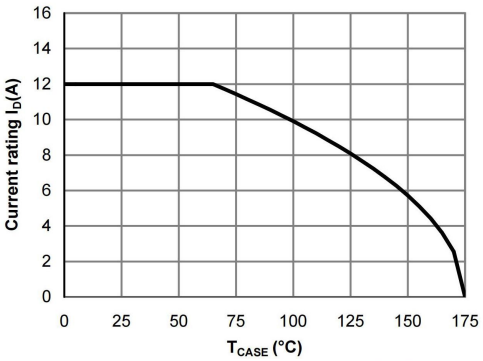



Figure 14: Current De-rating (Note F)

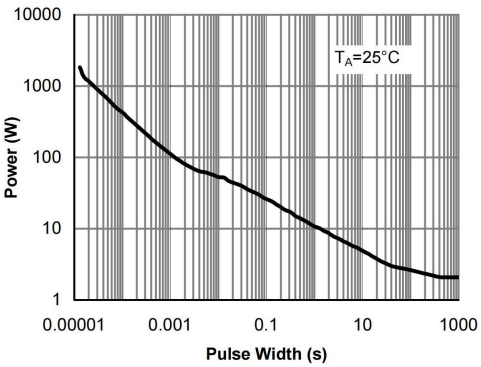



Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

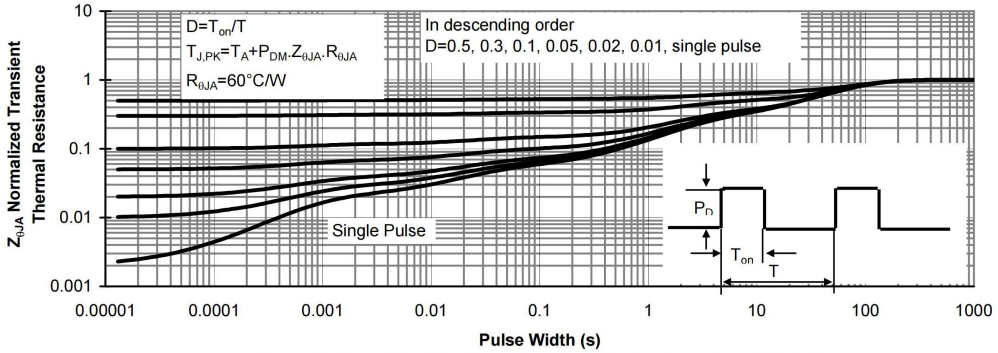
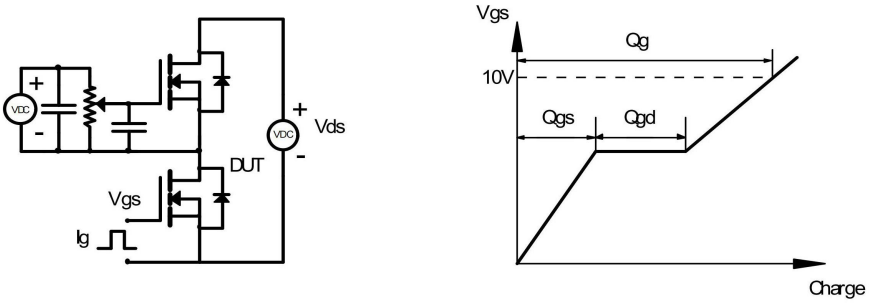


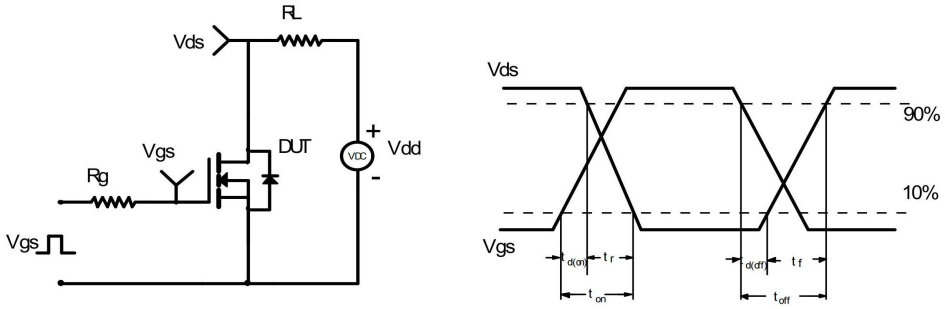

Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

# OM SENI

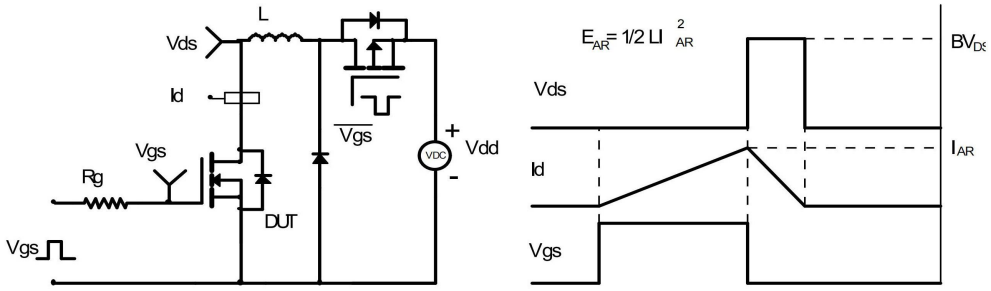
Gate Charge Test Circuit & Waveform




Resistive Switching Test Circuit & Waveforms




Unclamped Inductive Switching (UIS) Test Circuit & Waveforms




Diode Recovery Test Circuit & Waveforms

